

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT

(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.

SETI-0007

In Re Application: Shur et al.

Serial No.

10/696,693

Filing Date

10/29/2003

Examiner

Unknown

Group Art Unit

Unknown

METHOD OF RADIATION GENERATION AND MANIPULATION**Payment of Fee**

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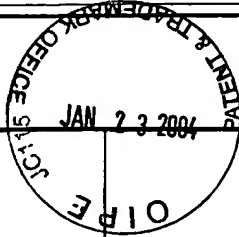
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Title: **METHOD OF RADIATION GENERATION AND MANIPULATION**

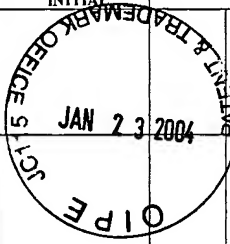
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37 CFR 1.97(b)

1. ☒ The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.

37 CFR 1.97(c)

2. ☐ The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:
- ☐ the statement specified in 37 CFR 1.97(e);
- OR**
- ☐ the fee set forth in 37 CFR 1.17(p).

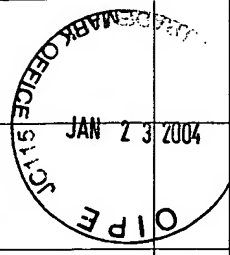
INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>		Docket Number (Optional) SETI-0007	Application Number 10/696,693
		Applicant(s) Shur et al.	
		Filing Date 10/29/2003	Group Art Unit Unkn wn
*EXAMINER INITIAL	OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>		
	"Coherent THz Emission in Semiconductors," Semiconductors and Semimetals, Chapt. 8, Vol. 67, 2001, pp.389-440.		
	"Conductance of Small Semiconductor Devices," A. A. Kastalsky et al. Solid State Comm., Vol. 39, No. 6, 1981, pp. 107-114.		
	"Impedance of Thin Semiconductor Films in Low Electric Field," K. Lee et al., Journal of Applied Physics, Vol. 54, No. 7, July 1983, pp. 4028-4034.		
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EXAMINER		DATE CONSIDERED	
<p>*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>			

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	"Far Infrared Emission from Plasma Oscillations of Si Inversion Layers," D.C. Tsui et al., Solid State Communications, Vol. 35, 1980, pp. 875-877.
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	"Narrow Channel 2-D MESFET for Low Power Electronics," W. C. B. Peatman et al., IEEE Transactions on Electron Devices, Vol. 42, No. 9, September 1995, pp. 1569-1573.

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	"Resonant Detection and Frequency Multiplication of Terahertz Radiation Utilizing Plasma Waves in Resonant-Tunneling Transistors," V. Ryzhii et al., Journal of Applied Physics, Vol. 88, No. 5, September 2000, pp. 2868-2871.		
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